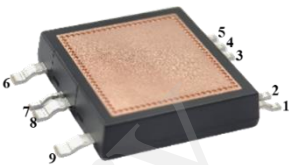


SiC Half-Bridge Module

PAAA07036FM

Features

- High Blocking Voltage with Low $R_{DS(on)}$
- High Temperature Operation
- Low Stray Inductance

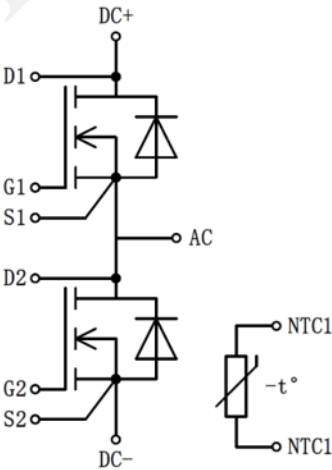


Applications

- Automotive Application
- EV/HEV

Standards Benefits

- Improve System Efficiency
- Improve Power Density
- Reduce System Size



Order Information

Part Number	Package	Marking
PAAA07036FM	IPM-MSOP9	PAAA07036FM

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PNJ Preliminary

1. Maximum Ratings

At $T_J = 25^\circ\text{C}$, unless specified otherwise

Parameter	Symbol	Value	Unit	Test Conditions
Drain - Source Voltage	V_{DSmax}	750	V	
Gate - Source Voltage (Dynamic)	V_{GSmax}	-10 / +22	V	AC (f > 1Hz)
Gate - Source Voltage(static) turn-on gate voltage turn-off gate voltage	$V_{GS,on}$ $V_{GS,off}$	+15/+18 -3	V	Static
Continuous Drain Current	I_D	36	A	$V_{GS} = 18\text{V}$ $T_c = 25^\circ\text{C}$ $T_J = 175^\circ\text{C}$
		26		$V_{GS} = 18\text{V}$ $T_c = 100^\circ\text{C}$ $T_J = 175^\circ\text{C}$
Power Dissipation	P_D	180	W	
Operating Junction Temperature	T_J	-55 To +175	$^\circ\text{C}$	
Storage Temperature	T_{stg}	-55 To +175	$^\circ\text{C}$	

2. Electrical Characteristics

At $T_J = 25^\circ\text{C}$, unless specified otherwise

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	750	/	/	V	$V_{GS} = 0V$
Gate Threshold Voltage	$V_{GS(th)}$	/	3.1	/	V	$V_{DS} = V_{GS}$ $I_D = 5.5mA$
Reverse Bias Drain Current	I_{DSS}	/	1.8	100	μA	$V_{GS} = 0V$ $V_{DS} = 750V$
Gate-Source Leakage Current	I_{GSS}	/	20	250	nA	$V_{GS} = 18V$ $V_{DS} = 0V$
Drain-Source On-State Resistance	$R_{DS(on)}$	/	55	70	m Ω	$V_{GS} = 18V$ $I_D = 20A$ $T_J = 25^\circ\text{C}$
		/	58	/		$V_{GS} = 18V$ $I_D = 20A$ $T_J = 175^\circ\text{C}$
		/	70	/		$V_{GS} = 18V$ $I_D = 20A$ $T_J = 25^\circ\text{C}$
Internal Gate Resistance	$R_{G(int)}$	/	1.2	/	Ω	$f = 1MHz$ $V_{AC} = 25mV$
Coss Stored Energy	E_{oss}	/	14	/	μJ	$V_{DS} = 400V$ $f = 1MHz$
Turn-on Energy	E_{on}	/	109	/	μJ	$V_{DS} = 400V$ $V_{GS} = -3/18V$ $I_D = 20A$ $R_G = 1\Omega$
Turn-off Energy	E_{off}	/	25	/		
Input Capacitance	C_{iss}	/	1853	/	pF	$V_{GS} = 0V$ $V_{DS} = 400V$
Output Capacitance	C_{oss}	/	141	/	pF	$f = 1MHz$ $V_{AC} = 25mV$

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Reverse Transfer Capacitance	C _{rss}	/	8.3	/	pF	
Gate to Source Charge	Q _{gs}	/	17.5	/	nC	
Gate to Drain Charge	Q _{gd}	/	15.3	/		
Total Gate Charge	Q _g	/	53.1	/		
Turn-On Delay Time	t _{d(on)}	/	16	/	ns	V _{DS} = 400V I _{DS} = 20A V _{GS} = -3 to 18V
Rise Time	t _r	/	20.1	/		
Turn-Off Delay Time	t _{d(off)}	/	22	/		
Fall Time	t _f	/	16	/		

3. Reverse Diode Characteristics

At $T_J = 25^\circ\text{C}$, unless specified otherwise

Parameter	Symbol	Value		Unit	Test Conditions
		Typ.	Max.		
Diode Forward Voltage	V_{SD}	5.2	/	V	$V_{GS} = -3V$ $I_{SD} = 20A$ $T_J = 25^\circ\text{C}$
		4.8	/	V	$V_{GS} = -3V$ $I_{SD} = 20A$ $T_J = 175^\circ\text{C}$
Continuous Diode Forward Current	I_S	29	/	A	$V_{GS} = -3V$
Peak Reverse Recovery Current	I_{rrm}	39	/	A	$V_{GS} = -3V$ $I_{SD} = 20A$ $V_R = 800V$ $dI/dt = 4100A/\mu s$ $T_J = 25^\circ\text{C}$

4. Thermal Characteristics

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Thermal Resistance from Junction to Cooling Fluid	$R_{\theta JF}$	/	0.92	/	$^\circ\text{C}/W$	

5. NTC Thermistor Characteristics

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ	Max.		
Rated Resistance	R_{NTC}	/	10	/	k Ω	$T_{NTC} = 25^{\circ}\text{C}$
Resistance Tolerance	$\Delta R/R$	-5	/	5	%	$T_{NTC} = 25^{\circ}\text{C}$
B-value	$B_{25/50}$	/	3380	/	K	$T_2 = 50^{\circ}\text{C}$
B-value	$B_{25/85}$	/	3435	/	K	$T_2 = 80^{\circ}\text{C}$
B-value	$B_{25/100}$	/	3485	/	K	$T_2 = 100^{\circ}\text{C}$
Power Dissipation	P_{NTC}	/	/	10	mW	$T_{NTC} = 25^{\circ}\text{C}$

6. Typical Performance

At $T_J = 25^\circ\text{C}$, unless specified otherwise

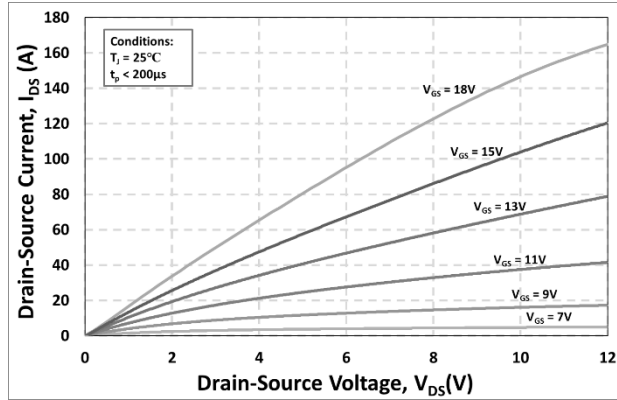


Figure 1. Output Characteristics $T_J = 25^\circ\text{C}$

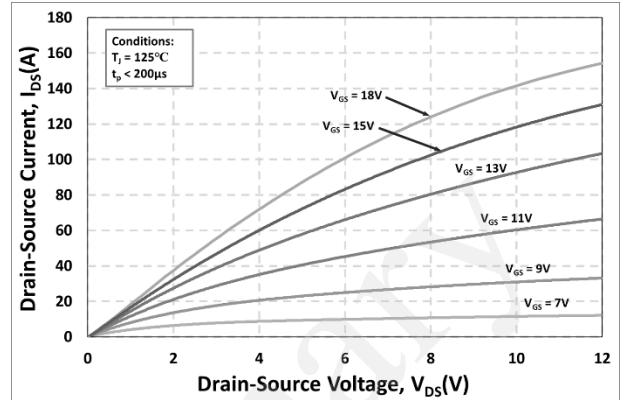


Figure 2. Output Characteristics $T_J = 125^\circ\text{C}$

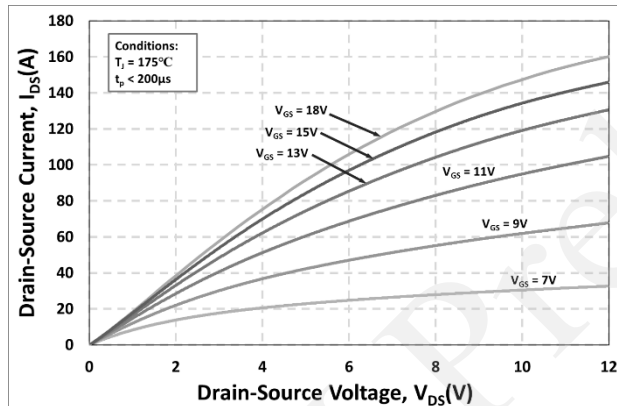


Figure 3. Output Characteristics $T_J = 175^\circ\text{C}$

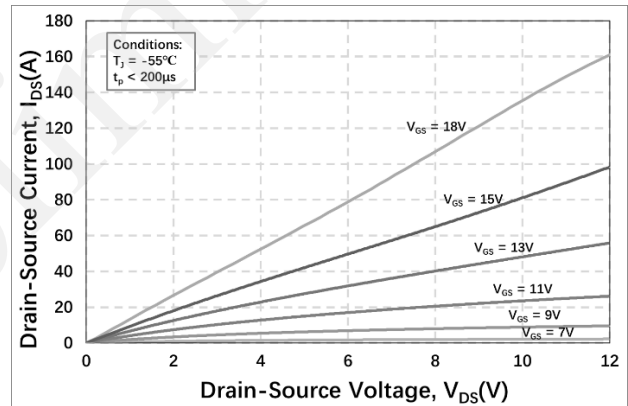


Figure 4. Output Characteristics $T_J = -55^\circ\text{C}$

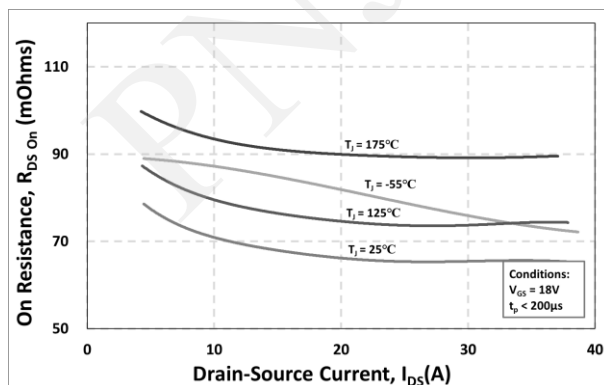


Figure 5. On-Resistance vs. Drain Current Various Temperatures

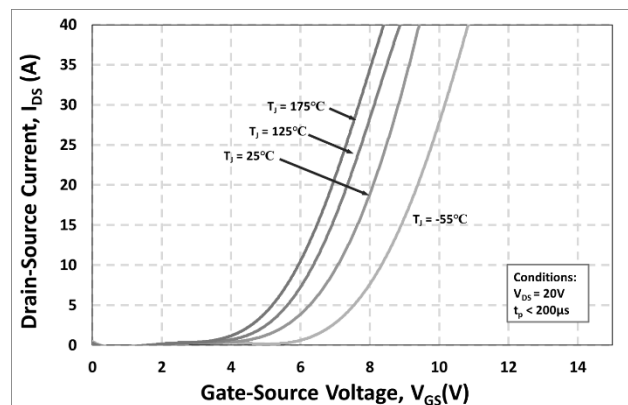


Figure 6. Transfer Characteristic for Various Junction Temperatures

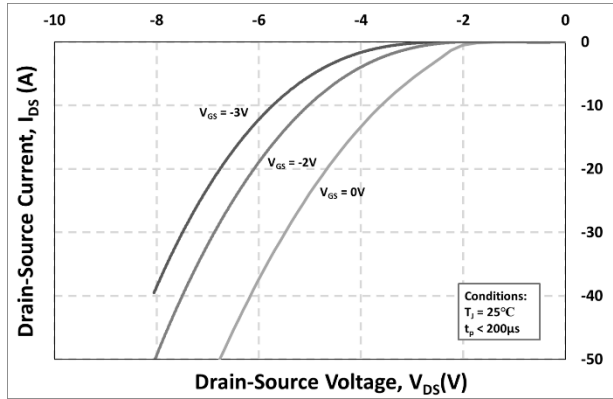


Figure 7. Body Diode Characteristic at 25°C

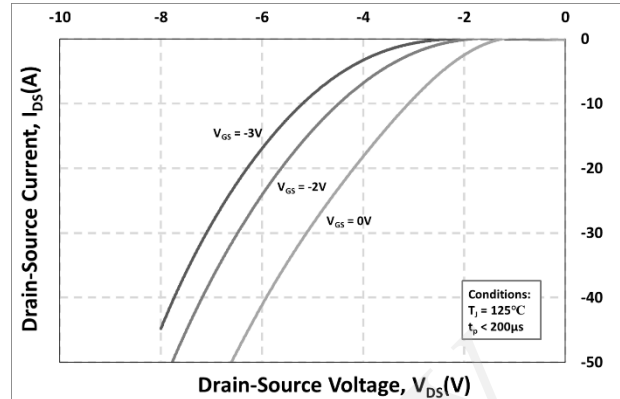


Figure 8. Body Diode Characteristic at 125°C

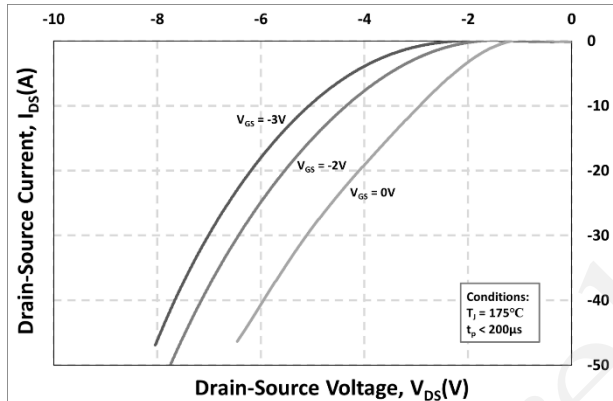


Figure 9. Body Diode Characteristic at 175°C

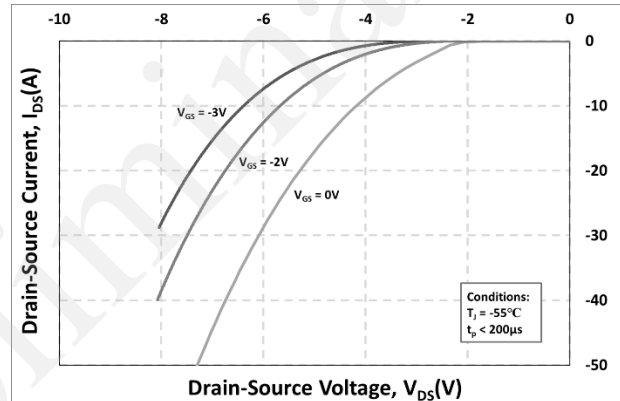


Figure 10. Body Diode Characteristic at -55°C

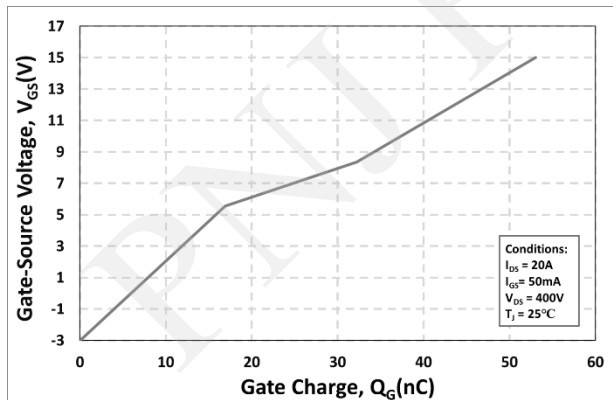


Figure 11. Gate Charge Characteristics

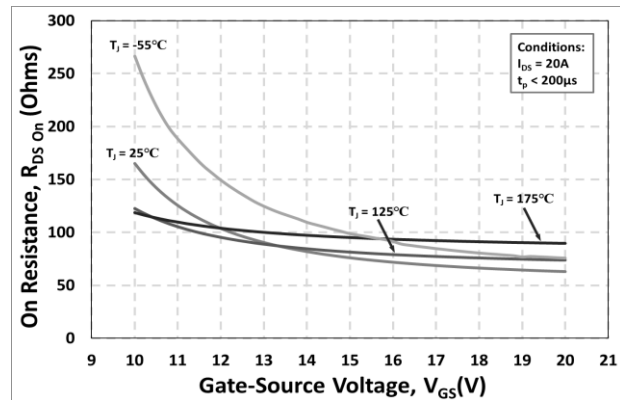


Figure 12. On-Resistance vs. Gate-Source Voltage

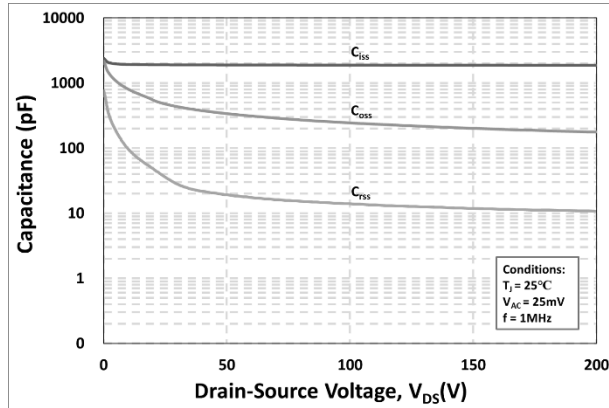


Figure 13. Capacitances vs. Drain-Source Voltage (0 - 200V)

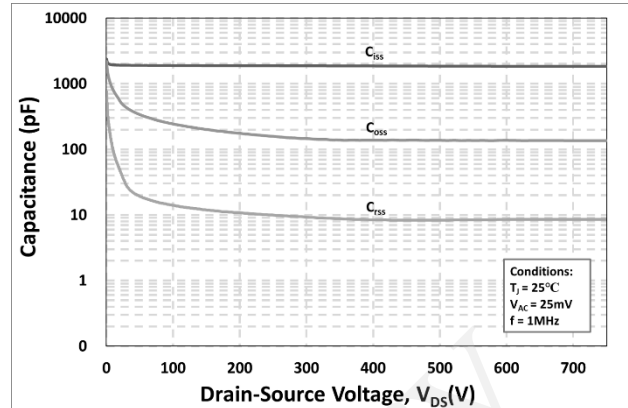


Figure 14. Capacitances vs. Drain-Source Voltage (0 - 750V)

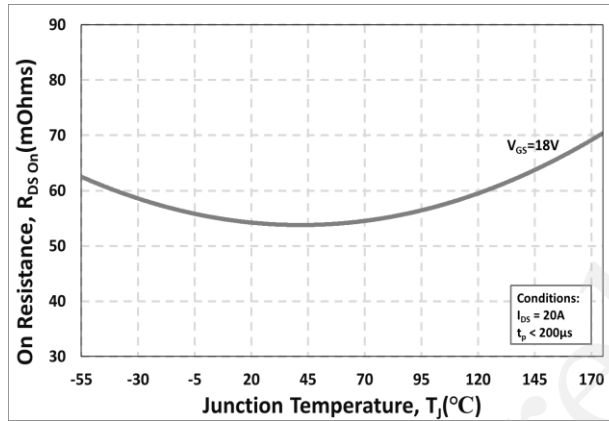


Figure 15. On-Resistance vs. Temperature

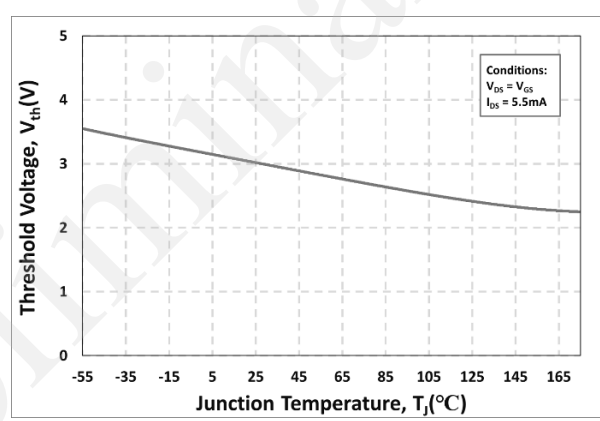
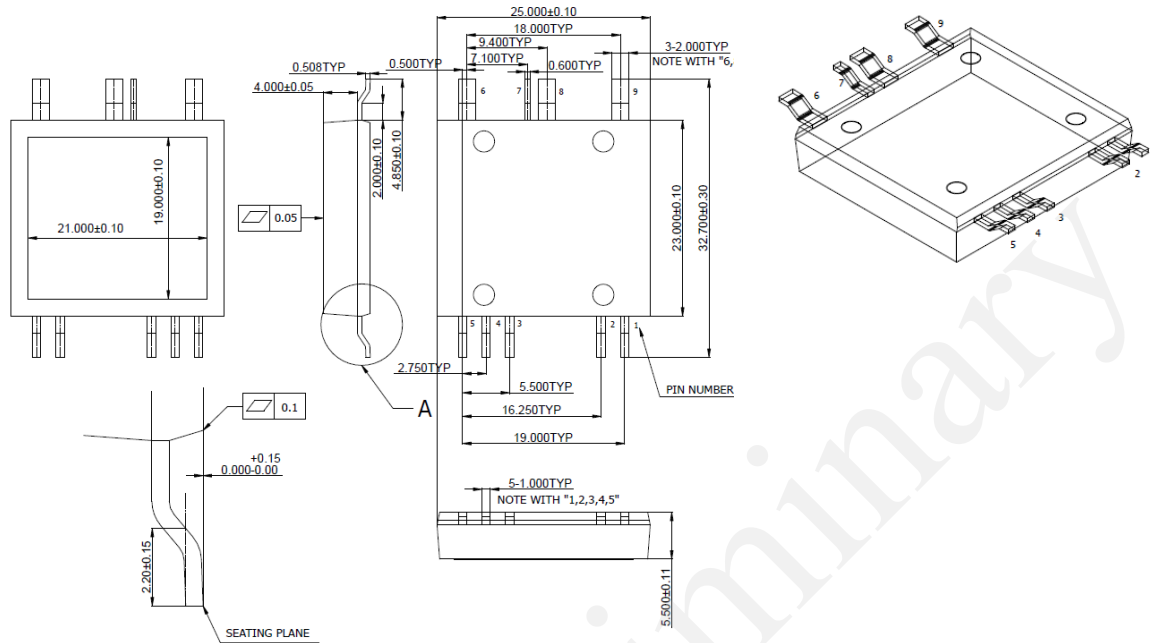


Figure 16. Threshold Voltage vs. Temperature

7. Package Outlines



DETAIL: "A"
4:1

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